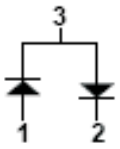
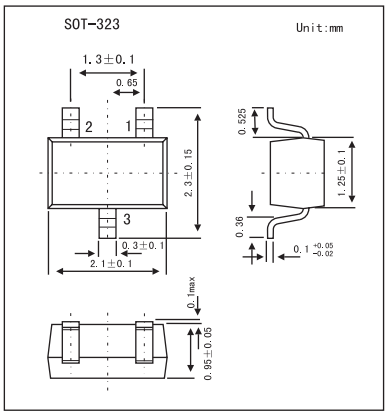
High Voltage Switching Diode
KMSD2004S(CMSD2004S)





■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Continuous reverse voltage	V_R	240	V
Peak repetitive reverse voltage	V_{RRM}	300	V
Peak repetitive reverse current	I_O	200	mA
Continuous forward current	I_F	225	mA
Peak repetitive forward current	I_{FRM}	625	mA
Forward surge current tp=1μs	I_{FSM}	4000	mA
tp=1s		1000	mA
Power dissipation	P_D	250	mW
Thermal Resistance.Junction-to-Ambient	R_{thJA}	500	℃/W
Operating and storage Junction temperature	T_J.T_{stg}	-65 to 150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	I_R=100μA	300			V
Forward Voltage	V_F	I_F = 100mA			-	V
Peak Reverse Current	I_R	V_R = 200V			-	nA
		V_R = 200V, T_A= 150℃			-	μA
		V_R = 240V			100	nA
		V_R = 240V, T_A= 150℃			100	μA
Junction Capacitance	C_j	V_R = 0, f = 1.0MHz			5	pF
Reverse Recovery Time	t_{rr}	I_F = I_R =30mA,Recov.to 3.0mA, R_L = 100 Ω			50	ns

■ Marking

Marking	B6D